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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	17
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg108f4-qfn24

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32TG108 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (⁰C)	Package
EFM32TG108F4-QFN24	4	2	32	1.98 - 3.8	-40 - 85	QFN24
EFM32TG108F8-QFN24	8	2	32	1.98 - 3.8	-40 - 85	QFN24
EFM32TG108F16-QFN24	16	4	32	1.98 - 3.8	-40 - 85	QFN24
EFM32TG108F32-QFN24	32	4	32	1.98 - 3.8	-40 - 85	QFN24

Visit **www.silabs.com** for information on global distributors and representatives.

2.1.11 Universal Synchronous/Asynchronous Receiver/Transmitter (US-ART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

2.1.12 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Autobaud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUARTTM, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output.

2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.16 Low Energy Timer (LETIMER)

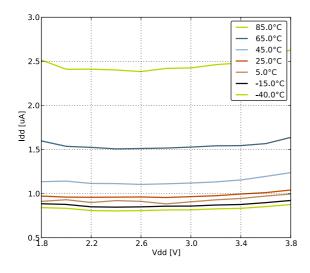
The unique LETIMERTM, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator. Figure 3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



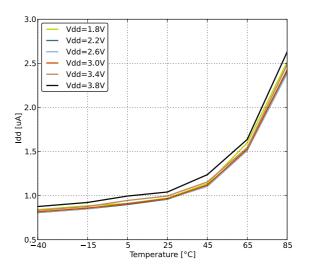


Figure 3.2. EM3 current consumption.

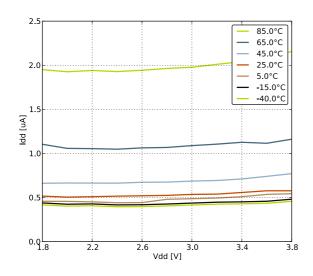
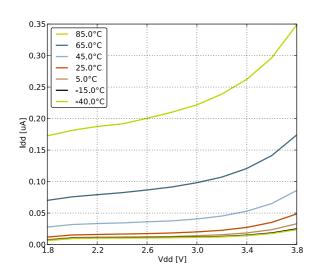
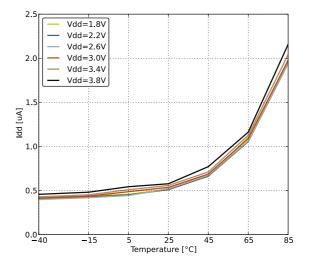
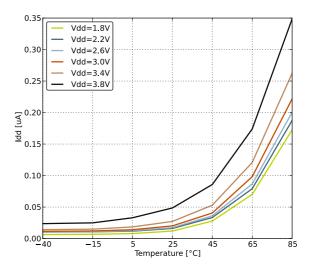


Figure 3.3. EM4 current consumption.







3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Тур	Max	Unit
t _{EM10}	Transition time from EM1 to EM0		0		HF- CORE- CLK cycles
t _{EM20}	Transition time from EM2 to EM0		2		μs
t _{EM30}	Transition time from EM3 to EM0		2		μs
t _{EM40}	Transition time from EM4 to EM0		163		μs

3.6 Power Management

The EFM32TG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{BODextthr} -	BOD threshold on falling external supply voltage		1.74		1.96	V
V _{BODextthr+}	BOD threshold on rising external sup- ply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external sup- ply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capaci- tor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
		T _{AMB} <150°C	10000			h
RET _{FLASH}	Flash data retention	T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) pro- gramming time		20			μs
t _{P_ERASE}	Page erase time		20	20.4	20.8	ms
t _{D_ERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage dur- ing flash erase and write		1.98		3.8	V

¹Measured at 25°C

3.8 General Purpose Input Output

Table 3.7. GPIO

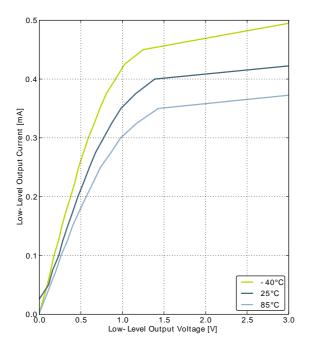
Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
V _{IOOH}	Output high volt- age (Production test condition = 3.0V, DRIVEMODE =	Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
	STANDARD)	Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V



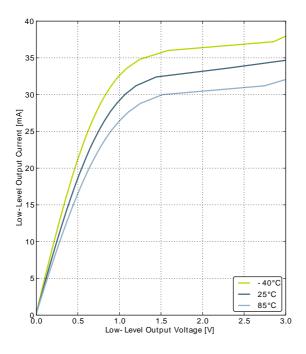
Symbol	Parameter	Condition	Min	Тур	Max	Unit
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
		Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
V _{IOOL}	Output low voltage (Production test condition = 3.0V,	Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
VIOOL	DRIVEMODE = STANDARD)	Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V
		Sinking 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.20V _{DD}	V
I _{IOLEAK}	Input leakage cur- rent	High Impedance IO connected to GROUND or V_{DD}		±0.1	±100	nA
R _{PU}	I/O pin pull-up resis- tor			40		kOhm
R _{PD}	I/O pin pull-down re- sistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
t _{IOGLITCH}	Pulse width of puls- es to be removed by the glitch sup- pression filter		10		50	ns
		GPIO_Px_CTRL DRIVEMODE = LOWEST and load capaci- tance C_L =12.5-25pF.	20+0.1C _L		250	ns
t _{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C_L =350-600pF	20+0.1C _L		250	ns
V _{IOHYST}	I/O pin hysteresis (V _{IOTHR+} - V _{IOTHR-})	V _{DD} = 1.98 - 3.8 V	0.1V _{DD}			V



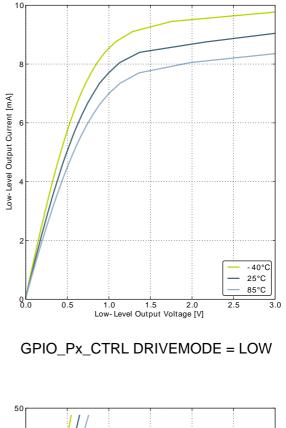
Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage

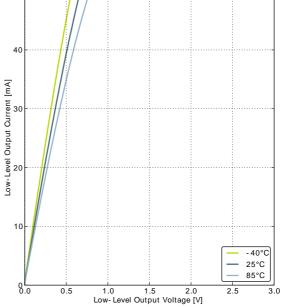


GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD

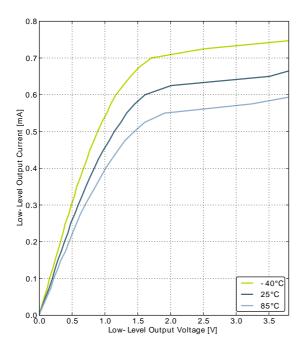




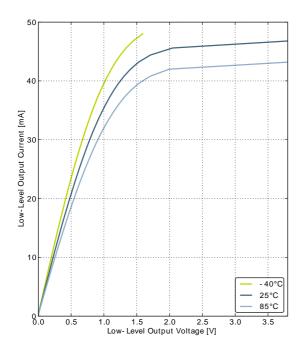
GPIO_Px_CTRL DRIVEMODE = HIGH



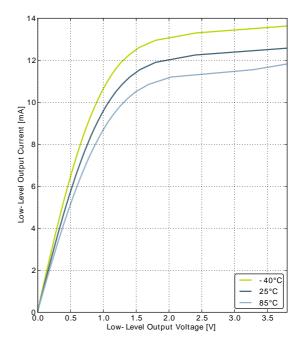
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



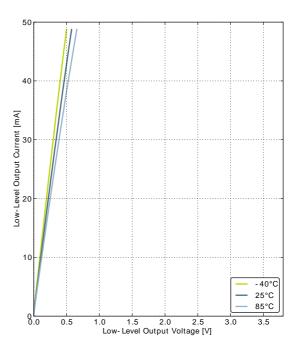
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR _{LFXO}	Supported crystal equivalent series re- sistance (ESR)			30	120	kOhm
C _{LFXOL}	Supported crystal external load range		X ¹		25	pF
I _{LFXO}	Current consump- tion for core and buffer after startup.	ESR=30 kOhm, C _L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t _{LFXO}	Start- up time.	ESR=30 kOhm, C _L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

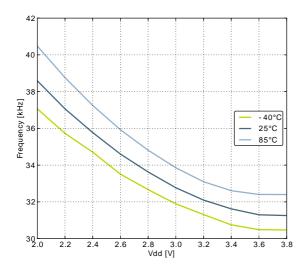
Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{HFXO}	Supported nominal crystal Frequency		4		32	MHz
500	Supported crystal	Crystal frequency 32 MHz		30	60	Ohm
ESR _{HFXO}	equivalent series re- sistance (ESR)	Crystal frequency 4 MHz		400	1500	Ohm
g _{mHFXO}	The transconduc- tance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C _{HFXOL}	Supported crystal external load range		5		25	pF
1	Current consump- tion for HFXO after startup	4 MHz: ESR=400 Ohm, C _L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μΑ
I _{HFXO}		32 MHz: ESR=30 Ohm, C _L =10 pF, HFXOBOOST in CMU_CTRL equals $0b11$		165		μΑ
t _{HFXO}	Startup time	32 MHz: ESR=30 Ohm, $C_L=10 \text{ pF}$, HFXOBOOST in CMU_CTRL equals 0b11		400		μs

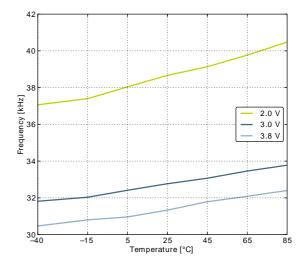
3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFRCO}	Oscillation frequen- cy , V_{DD} = 3.0 V, T_{AMB} =25°C		31.29	32.768	34.24	kHz
t _{LFRCO}	Startup time not in- cluding software calibration			150		μs
I _{LFRCO}	Current consump- tion			210	380	nA
TUNESTEP _L . FRCO	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage





3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		28 MHz frequency band	27.16	28.0	28.84	MHz
		21 MHz frequency band	20.37	21.0	21.63	MHz
£	Oscillation frequen-	14 MHz frequency band	13.58	14.0	14.42	MHz
t _{HFRCO}	су, V _{DD} = 3.0 V, Т _{АМВ} =25°С	11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40 ¹	6.60 ¹	6.80 ¹	MHz
		1 MHz frequency band	1.16 ²	1.20 ²	1.24 ²	MHz
t _{HFRCO_settling}	Settling time after start-up	f _{HFRCO} = 14 MHz		0.6		Cycles
	Current consump-	f _{HFRCO} = 28 MHz		160	190	μA
I _{HFRCO}	tion (Production test condition = 14 MHz)	f _{HFRCO} = 21 MHz		125	155	μA



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Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{RTC}	RTC current	RTC idle current, clock enabled		40		nA
I _{GPIO}	GPIO current	GPIO idle current, clock en- abled		5.31		μΑ/ MHz
I _{PRS}	PRS current	PRS idle current		2.81		μΑ/ MHz
I _{DMA}	DMA current	Clock enable		8.12		μΑ/ MHz



Figure 5.2. QFN24 PCB Solder Mask

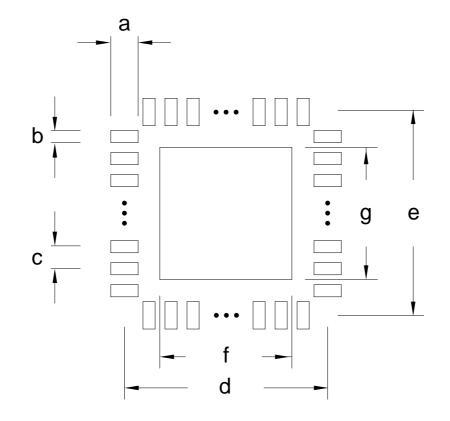


Table 5.2. QFN24 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Dim. (mm)
а	0.92	е	5.00
b	0.42	f	3.72
с	0.65	g	3.72
d	5.00	-	-



Figure 5.3. QFN24 PCB Stencil Design

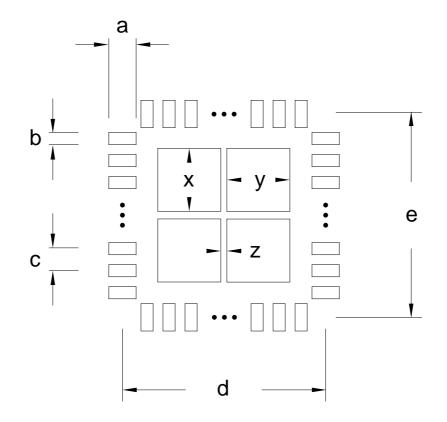


Table 5.3. QFN24 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Dim. (mm)
а	0.60	е	5.00
b	0.25	х	1.00
с	0.65	У	1.00
d	5.00	Z	0.50

- 1. The drawings are not to scale.
- 2. All dimensions are in millimeters.
- 3. All drawings are subject to change without notice.
- 4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
- 5. Stencil thickness 0.125 mm.
- 6. For detailed pin-positioning, see Figure 4.2 (p. 34).

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

7 Revision History

7.1 Revision 1.40

March 6th, 2015

Updated Block Diagram.

Updated Energy Modes current consumption.

Updated Power Management section.

Updated LFRCO and HFRCO sections.

Added AUXHFRCO to block diagram and Electrical Characteristics.

Corrected unit to kHz on LFRCO plots y-axis.

Updated ACMP section and the response time graph.

Updated VCMP section.

Updated Package dimensions table.

Updated Digital Peripherals section.

7.2 Revision 1.30

July 2nd, 2014

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated current consumption.

Updated transition between energy modes.

Updated power management data.

Updated GPIO data.

Updated LFXO, HFXO, HFRCO and ULFRCO data.

Updated LFRCO and HFRCO plots.

Updated ACMP data.

7.3 Revision 1.21

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

7.4 Revision 1.20

September 30th, 2013

Added I2C characterization data.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Document changed status from "Preliminary".

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.10

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Added GPIO_EM4WU3, GPIO_EM4WU4 and GPIO_EM4WU5 pins and removed GPIO_EM4WU1 in the Alternate functionality overview table.

Other minor corrections.

7.7 Revision 0.96

May 4th, 2012

Corrected PCB footprint figures and tables.

7.8 Revision 0.95

February 27th, 2012

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level and corrected Thermometer output gradient in Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added reference to errata document.

7.9 Revision 0.92

July 22nd, 2011

Updated current consumption numbers from latest device characterization data.

7.10 Revision 0.91

February 4th, 2011

Corrected max DAC sampling rate.

Increased max storage temperature.

Added data for <150°C and <70°C on Flash data retention.

Changed latch-up sensitivity test description.

Added IO leakage current.

Added Flash current consumption.

Updated HFRCO data.

Updated LFRCO data.

7.11 Revision 0.90

December 1st, 2010

New peripherals added to pinout, including LESENSE and OpAmps.

7.12 Revision 0.50

May 25th, 2010

Block diagram update.

7.13 Revision 0.40

March 26th, 2010

Initial preliminary release.

A Disclaimer and Trademarks

A.1 Disclaimer

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B Contact Information

Silicon Laboratories Inc. 400 West Cesar Chavez Austin, TX 78701

Please visit the Silicon Labs Technical Support web page: http://www.silabs.com/support/pages/contacttechnicalsupport.aspx and register to submit a technical support request.

List of Figures

2.1. Block Diagram	. 3
2.2. EFM32TG108 Memory Map with largest RAM and Flash sizes	. 7
3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.	10
3.2. EM3 current consumption.	10
3.3. EM4 current consumption	10
3.4. Typical Low-Level Output Current, 2V Supply Voltage	14
3.5. Typical High-Level Output Current, 2V Supply Voltage	15
3.6. Typical Low-Level Output Current, 3V Supply Voltage	
3.7. Typical High-Level Output Current, 3V Supply Voltage	
3.8. Typical Low-Level Output Current, 3.8V Supply Voltage	
3.9. Typical High-Level Output Current, 3.8V Supply Voltage	
3.10. Calibrated LFRCO Frequency vs Temperature and Supply Voltage	
3.11. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature	
3.12. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature	
3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature	
3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature	
3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature	
3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature	
3.17. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1	
4.1. EFM32TG108 Pinout (top view, not to scale)	
4.2. QFN24	
5.1. QFN24 PCB Land Pattern	
5.2. QFN24 PCB Solder Mask	
5.3. QFN24 PCB Stencil Design	
6.1. Example Chip Marking (top view)	38

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